

TOSHIBA TRANSISTOR SILICON NPN EPITAXIAL TYPE (PCT PROCESS)

2SC3265

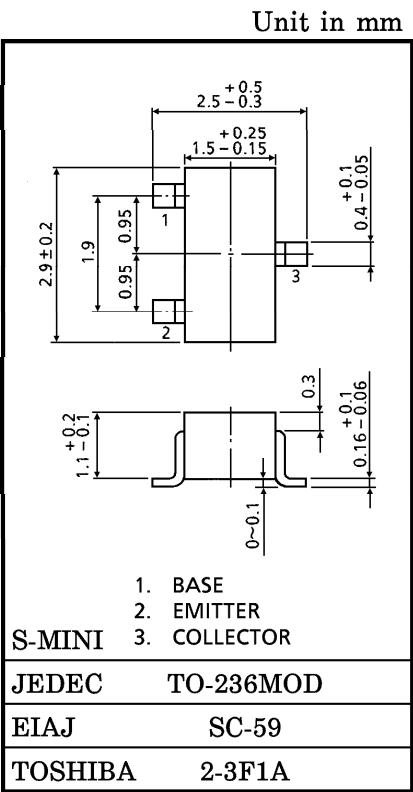
LOW FREQUENCY POWER AMPLIFIER APPLICATIONS

POWER SWITCHING APPLICATIONS

- High DC Current Gain :  $h_{FE}(1) = 100\sim320$
- Low Saturation Voltage :  $V_{CE(sat)} = 0.4\text{ V (Max.)}$   
( $I_C = 500\text{ mA}$ ,  $I_B = 20\text{ mA}$ )
- Complementary to 2SA1298

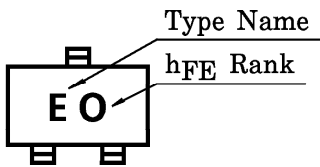
MAXIMUM RATINGS ( $T_a = 25^{\circ}\text{C}$ )

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	$V_{CBO}$	30	V
Collector-Emitter Voltage	$V_{CEO}$	25	V
Emitter-Base Voltage	$V_{EBO}$	5	V
Collector Current	$I_C$	800	mA
Base Current	$I_B$	160	mA
Collector Power Dissipation	$P_C$	200	mW
Junction Temperature	$T_j$	150	$^{\circ}\text{C}$
Storage Temperature Range	$T_{stg}$	$-55\sim150$	$^{\circ}\text{C}$



Weight : 0.012 g

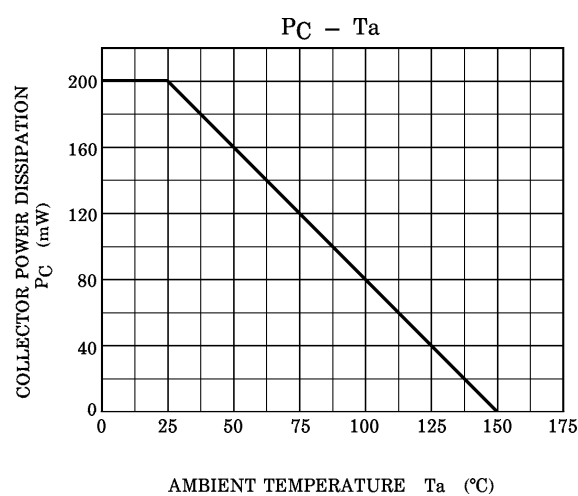
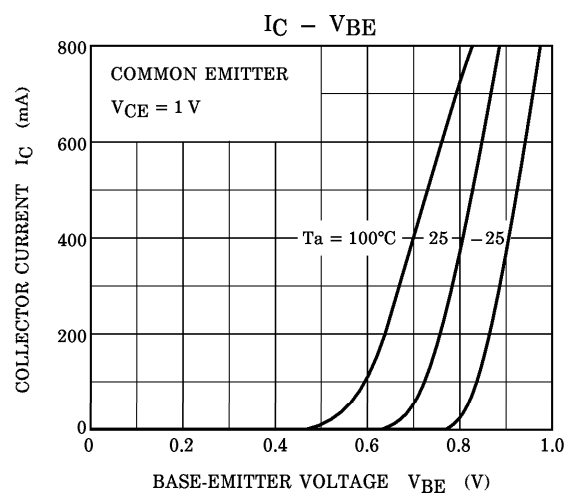
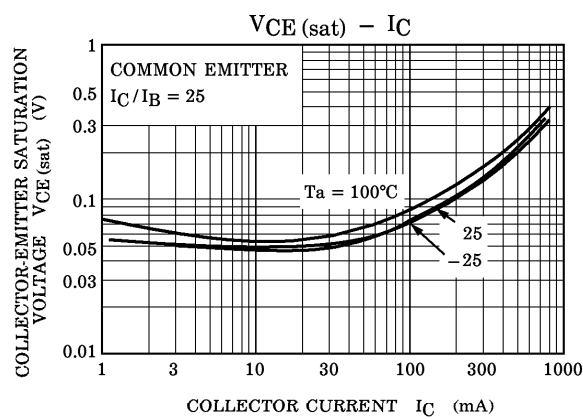
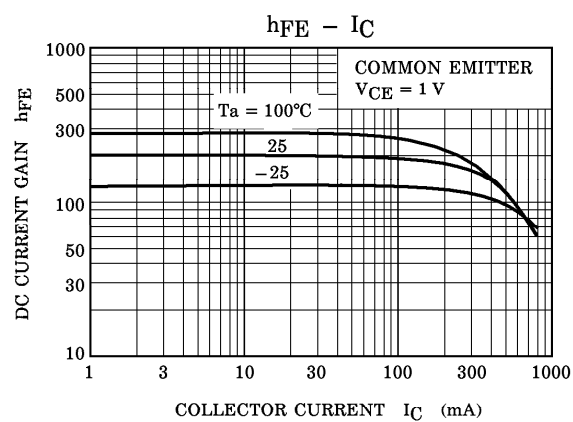
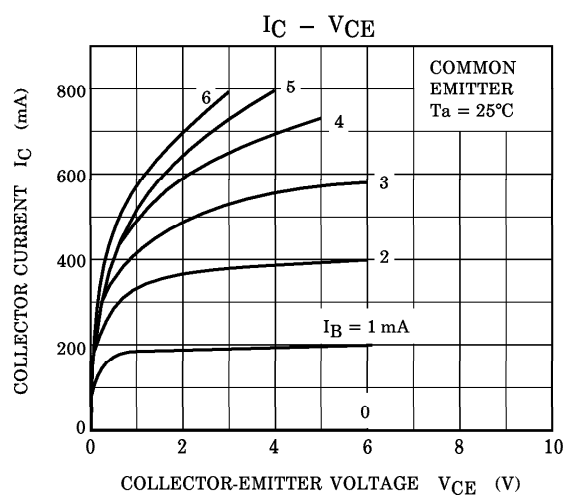
MARKING



## ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	$I_{CBO}$	$V_{CB} = 30\text{ V}, I_E = 0$	—	—	0.1	$\mu\text{A}$
Emitter Cut-off Current	$I_{EBO}$	$V_{EB} = 5\text{ V}, I_C = 0$	—	—	0.1	$\mu\text{A}$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = 10\text{ mA}, I_B = 0$	25	—	—	V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E = 0.1\text{ mA}, I_C = 0$	5	—	—	V
DC Current Gain	$h_{FE(1)}$ (Note)	$V_{CE} = 1\text{ V}, I_C = 100\text{ mA}$	100	—	320	
	$h_{FE(2)}$	$V_{CE} = 1\text{ V}, I_C = 800\text{ mA}$	40	—	—	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 500\text{ mA}, I_B = 20\text{ mA}$	—	—	0.4	V
Base-Emitter Voltage	$V_{BE}$	$V_{CE} = 1\text{ V}, I_C = 10\text{ mA}$	0.5	—	0.8	V
Transition Frequency	$f_T$	$V_{CE} = 5\text{ V}, I_C = 10\text{ mA}$	—	120	—	MHz
Collector Output Capacitance	$C_{ob}$	$V_{CB} = 10\text{ V}, I_E = 0, f = 1\text{ MHz}$	—	13	—	pF

Note :  $h_{FE(1)}$  Classification    O : 100~200,    Y : 160~320



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